

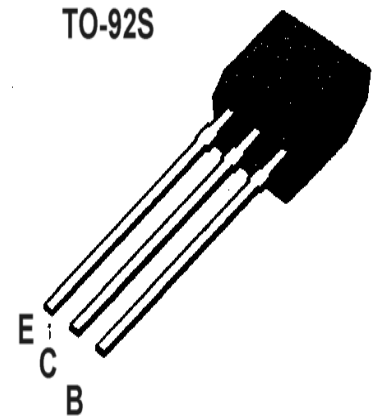
PNP Transistors

—PNP Silicon—

APPLICATION: AF Power Amplifier, Medium-Speed Switching,
 Small-sized Motor Drivers.

MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V_{CB0}	-15	V
Collector-emitter voltage	V_{CEO}	-15	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_c	-0.8	A
Collector current	I_{cp}	-3	A
Collector Power Dissipation	P_c	0.3	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55~150	$^\circ\text{C}$


ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$, $R_G=10\Omega$)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION		
Collector-Base Breakdown Voltage	BV_{cbo}	-15			V	$I_c=-10\mu\text{A}$	$I_e=0$	
Collector-Emitter Breakdown Voltage	BV_{ceo}	-15			V	$I_c=-1\text{mA}$	$I_b=0$	
Emitter-Base Breakdown Voltage	BV_{ebo}	-5			V	$I_e=-10\mu\text{A}$	$I_c=0$	
Collector Cut-off Current	I_{cbo}			-0.1	μA	$V_{cb}=-12\text{V}$	$I_e=0$	
Emitter Cut-off Current	I_{ebo}			-0.1	μA	$V_{eb}=-4\text{V}$	$I_c=0$	
Base-Emitter Saturation Voltage	$V_{be(sat)}$		-0.9	-1.2	V	$I_c=-0.4\text{A}$	$I_b=-20\text{mA}$	
Collector-Emitter Saturation Voltage	$V_{ce(sat)}$		-0.1	-0.2	V	$I_c=-0.4\text{A}$	$I_b=-20\text{mA}$	
DC Current Gain	h_{FE}	140		560	β	$V_{ce}=-2\text{V}$	$I_c=-50\text{mA}$	
Gain bandwidth product	f_T		300		MHz	$V_{ce}=-2\text{V}$	$I_c=-50\text{mA}$	
Common Base Output Capacitance	C_{ob}		15		pF	$V_{cb}=-10\text{V}$	$I_e=0$	$f=1\text{MHz}$

HFEC Classification And Marking

Print Mark	B1296S		
Classification	S	T	U
h_{FE}	140~280	200~400	280~560